

L Number	Hits	Search Text	DB	Time stamp
3	1385	(P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))	USPAT; US-PGPUB	2001/08/03 17:00
4	17824	(P\$2source ("P" adj7 source))	USPAT; US-PGPUB	2001/08/03 17:00
5	38650	gate adj3 electrode	USPAT; US-PGPUB	2001/08/03 17:00
6	2772	(P\$3polysilicon ("P" adj8 polysilicon))	USPAT; US-PGPUB	2001/08/03 17:01
7	433	((P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))) and ((P\$2source ("P" adj7 source)))	USPAT; US-PGPUB	2001/08/03 16:19
8	175	((P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))) and ((P\$2source ("P" adj7 source))) and (gate adj3 electrode)	USPAT; US-PGPUB	2001/08/03 16:19
9	37	((P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))) and ((P\$2source ("P" adj7 source))) and (gate adj3 electrode) and ((P\$3polysilicon ("P" adj8 polysilicon)))	USPAT; US-PGPUB	2001/08/03 16:23
10	400245	substrate wafer	USPAT; US-PGPUB	2001/08/03 17:01
11	161409	(substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))	USPAT; US-PGPUB	2001/08/03 17:02
12	57134	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)	USPAT; US-PGPUB	2001/08/03 17:02
13	14385	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4) and epitaxial	USPAT; US-PGPUB	2001/08/03 17:02
14	11343	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4) and epitaxial) and (boron "B")	USPAT; US-PGPUB	2001/08/03 17:03
15	10399	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4) and epitaxial) and (boron "B")) and (phosphrous "P")	USPAT; US-PGPUB	2001/08/03 17:03
16	2833	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4) and epitaxial) and (boron "B")) and (phosphrous "P")) and (P\$2channel\$2 ("P" adj2 channel) P?channel)	USPAT; US-PGPUB	2001/08/03 17:04
17	1381	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4) and epitaxial) and (boron "B")) and (phosphrous "P")) and (P\$2channel\$2 ("P" adj2 channel) P?channel)) and anneal\$3	USPAT; US-PGPUB	2001/08/03 16:36
18	351	(P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))	EPO; JPO; DERWENT;	2001/08/03 17:00
19	7629	(P\$2source ("P" adj7 source))	IBM TDB EPO; JPO; DERWENT;	2001/08/03 17:00
20	73183	gate adj3 electrode	IBM TDB EPO; JPO; DERWENT;	2001/08/03 17:01
21	1220	(P\$3polysilicon ("P" adj8 polysilicon))	IBM TDB EPO; JPO; DERWENT;	2001/08/03 17:01
22	0	((P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))) and ((P\$2source ("P" adj7 source))) and (gate adj3 electrode) and ((P\$3polysilicon ("P" adj8 polysilicon)))	IBM TDB EPO; JPO; DERWENT;	2001/08/03 17:01
23	9	((P\$2substrat\$3 ("P" adj3 tupe adj2 substrate))) and ((P\$2source ("P" adj7 source))) and (gate adj3 electrode)	IBM TDB EPO; JPO; DERWENT;	2001/08/03 17:01
24	1094018	substrate wafer	IBM TDB EPO; JPO; DERWENT;	2001/08/03 17:02

25	236460	(substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))	EPO; JPO; DERWENT; IBM TDB	2001/08/03 17:02
26	26997	((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)	EPO; JPO; DERWENT; IBM TDB	2001/08/03 17:02
27	2563	((((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)) and epitaxial	EPO; JPO; DERWENT; IBM TDB	2001/08/03 17:03
28	1341	(((((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)) and epitaxial) and (boron "B")	EPO; JPO; DERWENT; IBM TDB	2001/08/03 17:03
29	849	(((((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)) and epitaxial) and (boron "B")) and (phosphrous "P")	EPO; JPO; DERWENT; IBM TDB	2001/08/03 17:03
30	56	((((((substrate wafer) and (dielectric insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)) and epitaxial) and (boron "B")) and (phosphrous "P")) and (P\$2channel\$2 ("P" adj2 channel) P?channel)	EPO; JPO; DERWENT; IBM TDB	2001/08/03 17:04